IN THE SPECIFICATION:

Please replace paragraph number **[0002]** with the following rewritten paragraph:

[0002] This application is a continuation of application Serial No. 10/114,492, filed April 2, 2002, ~~pending~~ now U.S. Patent 6,589,803, issued July 8, 2003, which is a continuation of application Serial No. 09/788,984, filed February 20, 2001, now U.S. Patent 6,403,390, issued June 11, 2002, which is a continuation of application Serial No. 09/260,708, filed March 1, 1999, now U.S. Patent 6,197,607, issued March 6, 2001.

Please replace paragraph number **[0013]** with the following rewritten paragraph:

[0013] The second layer may be planarized by known processes, such as by ~~chemical~~ chemical-mechanical planarization or chemical-mechanical polishing ("CMP"). Upon planarization of the second layer, portions of the first layer disposed above each of the emitter tips are preferably exposed through the second layer.

Please replace paragraph number **[0018]** with the following rewritten paragraph:

[0018] The fourth layer may be planarized by known processes, such as by ~~chemical~~ chemical-mechanical planarization or by chemical-mechanical polishing techniques, to form the grid of the field emission array. As the fourth layer is planarized and dielectric material of the third layer is exposed therethrough, grid openings are formed through the fourth layer. Planarization may continue until the grid openings are of the desired size (e.g., diameter).

Please replace paragraph number **[0038]** with the following rewritten paragraph:

[0038] Referring now to FIG. 2, a layer 16 of dielectric material, which is also referred to herein as a first layer or as a first dielectric layer, may be disposed over substrate 12 and emitter tip 14. As illustrated, layer 16 is raised above emitter tip 14. Preferably, the thickness of layer 16 is less than the height of emitter tip 14 so as to facilitate the exposure of layer 16 through the subsequently deposited layer 18 (FIG. 3) during planarization of layer 18. In addition, the

thickness of layer 16 preferably facilitates the subsequent definition of a grid opening 26 (see FIG. 9) of desired size.

Please replace paragraph number **[0041]** with the following rewritten paragraph:

[0041] Turning to FIG. 3, another layer 18, which is also referred to herein as a second layer, is disposed over layer 16. As shown in FIG. 3, since layer 18 has a substantially consistent thickness, layer 18 includes upward protrusions 19 over each emitter tip 14. Layer 18 preferably comprises a material that may be planarized by known processes, such as by ~~chemical-~~ chemical-mechanical planarization or chemical-mechanical polishing. In addition, the material of layer 18 is preferably selectively etchable with respect to the dielectric material of layer 16 and with respect to the material of emitter tip 14. An exemplary material that may be employed as layer 18 is chromium, which may be deposited by known sputtering techniques.

Please replace paragraph number **[0044]** with the following rewritten paragraph:

[0044] Layer 18 may be planarized by known processes, such as by the ~~chemical-~~ chemical-mechanical planarization or chemical-mechanical polishing processes disclosed in United States Patents 4,193,226 and 4,811,522 (hereinafter "the '226 Patent" and "the '522 ~~Patent",~~Patent," respectively), the disclosures of both of which are hereby incorporated in their entireties by this reference. Preferably, layer 18 is planarized such that the combined thickness of layer 16 and layer 18 is at least the height of emitter tip 14.

Please replace paragraph number **[0048]** with the following rewritten paragraph:

[0048] FIG. 6 illustrates the substantial removal of layer 18 (FIG. 3) from layer 16. Layer 18 may be removed from layer 16 by known processes, such as by etching the material of layer 18. If an etchant is employed to remove the material of layer 18, the etchant is preferably selective for the material of layer 18 over the dielectric material of layer 16. As substantially all of layer 18 is removed from field emission array 10, a wet etch process and wet etchants are preferably employed, as the removal of layer 18 may not be selective and wet etchants typically exhibit greater selectivity than comparable dry etchants. Of course, dry etchants may also be

employed. After layer 18 has been substantially removed from field emission array 10, any etchants that were employed may be removed from field emission array 10 by known processes, such as by washing field emission array 10.

Please replace paragraph number **[0057]** with the following rewritten paragraph:

[0057] Layer 24 may be planarized by known processes, such as by the ~~chemical-~~ chemical-mechanical planarization or chemical-mechanical polishing processes disclosed in the '226 Patent and in the '522 Patent. Preferably, following the planarization of layer 24, the thickness of layer 24 is substantially a desired thickness for a grid of field emission array 10.